

AM PIN Diode

BAQ806

100V

DATASHEET

OEM – Philips

Source: Philips Databook 1999

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FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- UL 94V-O classified plastic package
- Shipped in 12 mm embossed tape.

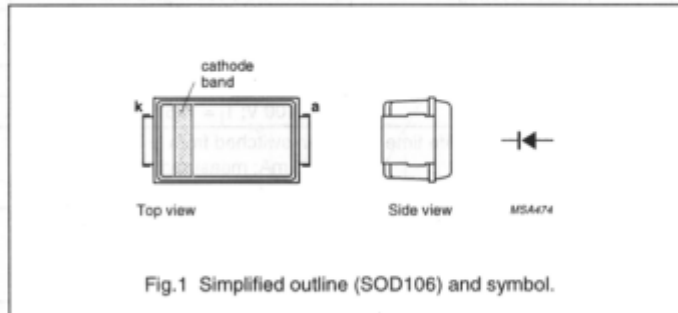
APPLICATIONS

- RF attenuator with low distortion for frequencies above 100 kHz.

DESCRIPTION

DO-214AC surface mountable package with glass passivated chip.

The well-defined void-free case is of a transfer-moulded thermo-setting plastic.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage	–	100	V
V_R	continuous reverse voltage	–	100	V
T_{stg}	storage temperature	–65	+175	°C
T_j	junction temperature	–65	+150	°C

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ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	$I_F = 100\text{ mA}$; see Figs 2 and 3	–	0.9	1.1	V
		$I_F = 100\text{ mA}$; $T_j = T_{j\text{max}}$; see Figs 2 and 3	–	0.7	0.9	V
I_R	reverse current	$V_R = 100\text{ V}$; see Fig. 4	–	–	0.1	μA
		$V_R = 100\text{ V}$; $T_j = 125\text{ °C}$; see Fig. 4	–	–	30	μA
τ	charge carrier life time	when switched from $I_F = 10\text{ mA}$ to $I_R = 6\text{ mA}$; measured at 10% of I_R ; see Fig. 13	15	25	–	μs
C_d	diode capacitance	$f = 1\text{ MHz}$; see Figs 5, 6, 7 and 8	–	9	11	pF
		$V_R = 0\text{ V}$ $V_R = 2\text{ V}$	–	5	6	pF
r_D	diode forward resistance	$f = 100\text{ kHz}$; see Figs 9 and 14	–	3300	6000	Ω
		$I_F = 10\text{ }\mu\text{A}$	–	560	900	Ω
		$I_F = 1\text{ mA}$	–	62	90	Ω
		$I_F = 10\text{ mA}$	–	7	10	Ω
r_s	diode series resistance	$f = 100\text{ kHz}$; see Figs 10, 11 and 12	–	–	–	–
		$V_R = 0\text{ V}$	1000	2100	–	$\text{k}\Omega$
		$V_R = 2\text{ V}$	5000	12000	–	$\text{k}\Omega$
		$f = 1\text{ MHz}$; see Figs 10, 11 and 12	–	–	–	–
		$V_R = 0\text{ V}$	25	50	–	$\text{k}\Omega$
		$V_R = 2\text{ V}$	100	250	–	$\text{k}\Omega$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{\text{th } j\text{-tp}}$	thermal resistance from junction to tie-point		25	K/W
$R_{\text{th } j\text{-a}}$	thermal resistance from junction to ambient	note 1	100	K/W
		note 2	150	K/W

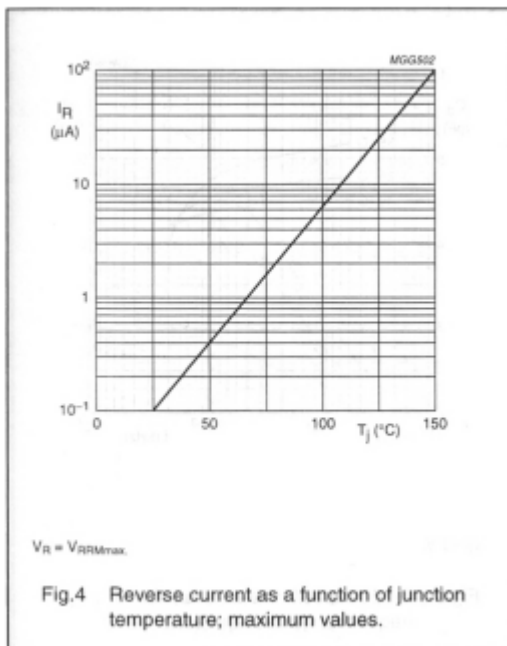
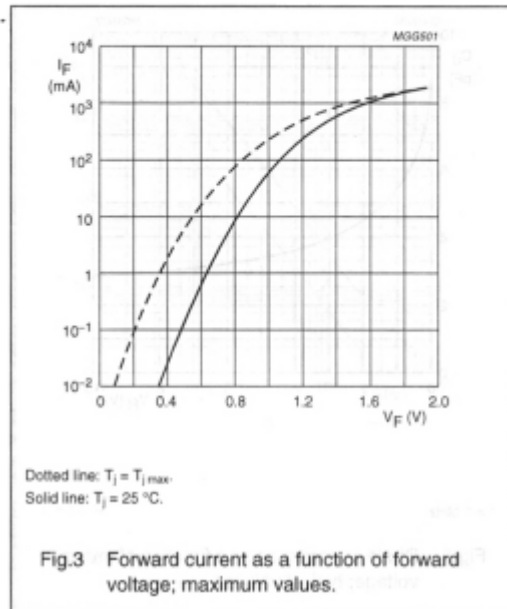
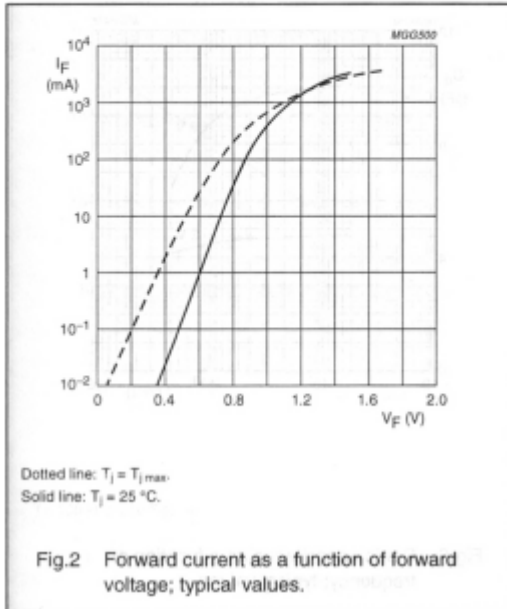
Note

- Device mounted on Al_2O_3 printed-circuit board, 0.7 mm thick; thickness of copper $\geq 35\text{ }\mu\text{m}$, see Fig. 15
- Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper $\geq 40\text{ }\mu\text{m}$, see Fig. 15.
For more information please refer to the 'General Part of Handbook SC10'

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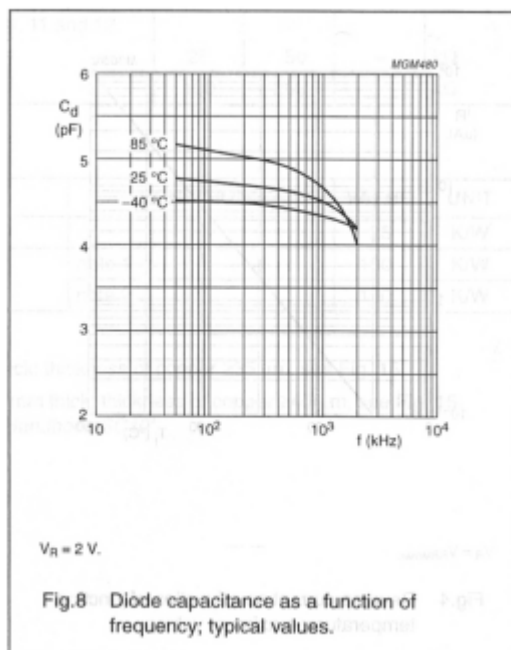
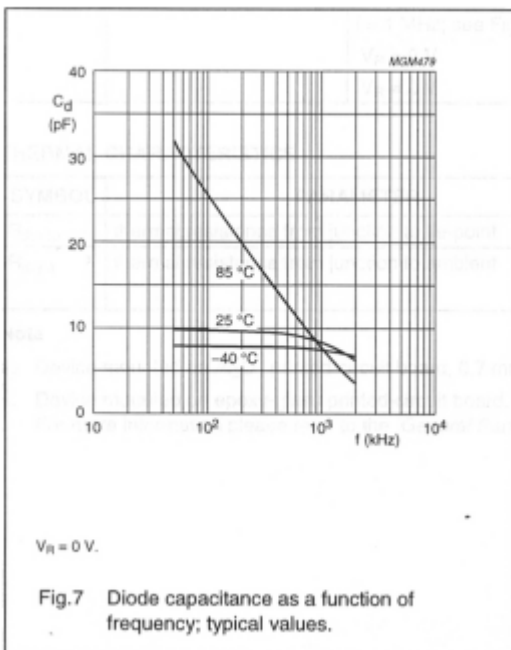
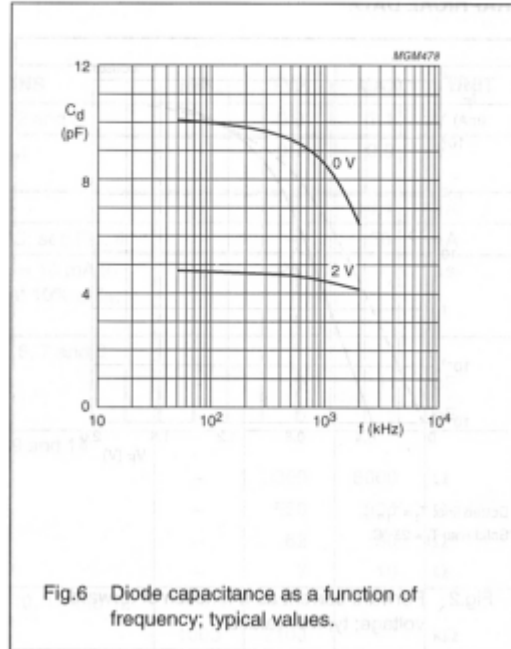
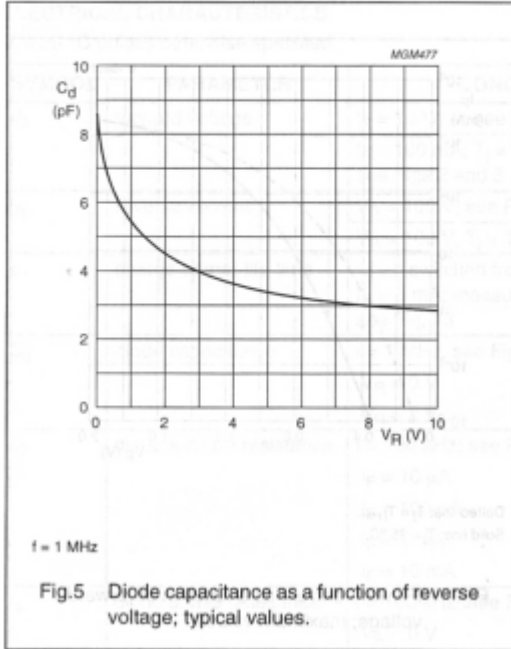
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GRAPHICAL DATA



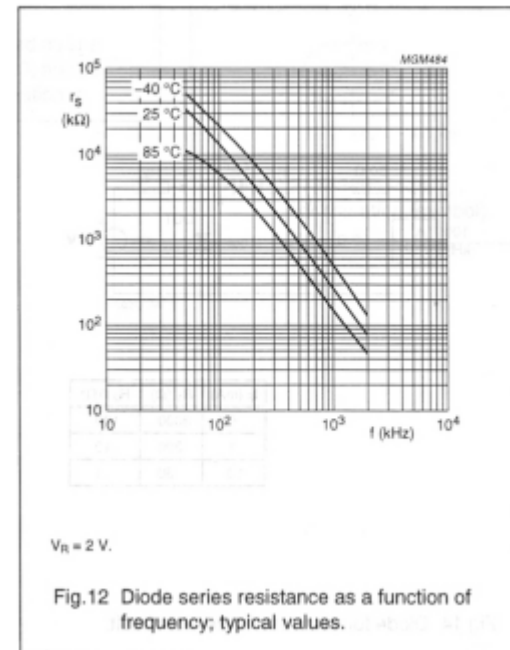
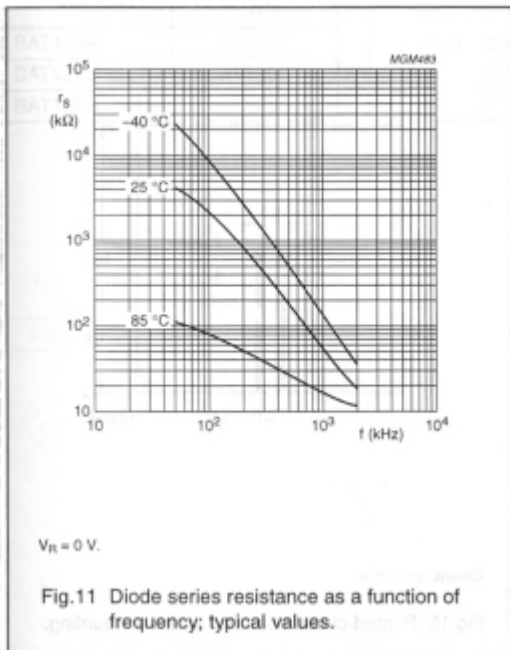
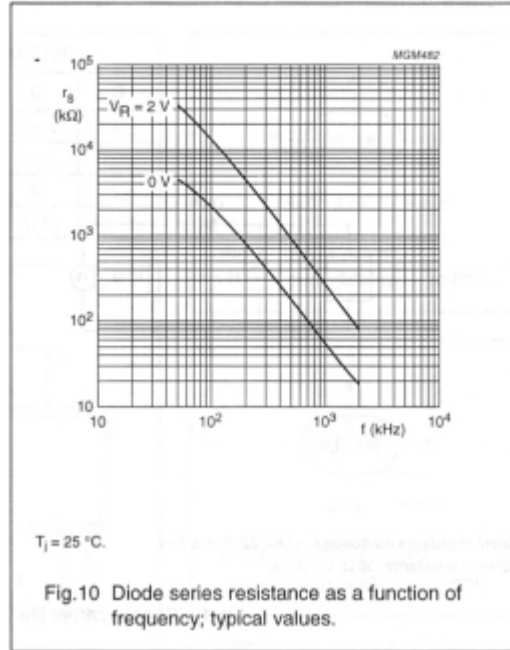
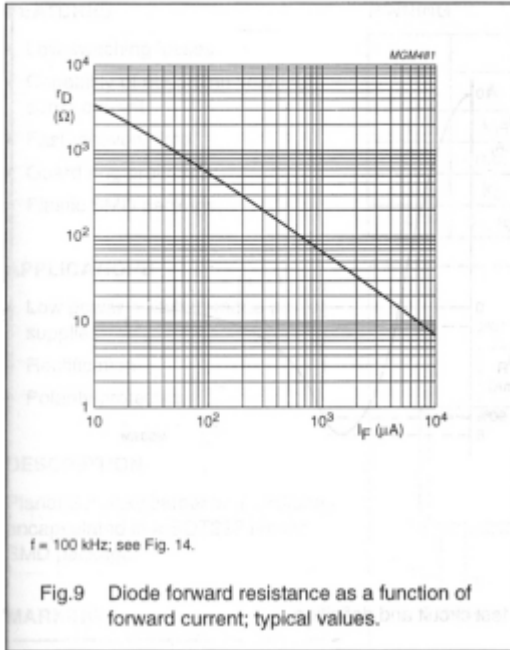
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